

## VS-10ETF10S-M3, VS-10ETF12S-M3 Series

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## Surface Mount Fast Soft Recovery Rectifier Diode, 10 A



PRIMARY CHARACTERISTICS						
I <sub>F(AV)</sub>	10 A					
$V_{R}$	1000 V, 1200 V					
V <sub>F</sub> at I <sub>F</sub>	1.33 V					
I <sub>FSM</sub>	155 A					
t <sub>rr</sub>	80 ns					
T <sub>J</sub> max.	150 °C					
Snap factor	0.6					
Package	D <sup>2</sup> PAK (TO-263AB)					
Circuit configuration	Single					

### **FEATURES**

· Glass passivated pellet chip junction



• Meets MSL level 1, per J-STD-020, LF maximum peak of 245 °C

COMPLIANT **HALOGEN** FREE

 Designed and qualified according

JEDEC®-JESD 47

 Material categorization: for definitions of compliance please see www.vishav.com/doc?99912

#### **APPLICATIONS**

- Output rectification and freewheeling in inverters, choppers and converters
- Input rectifications where severe restrictions on conducted EMI should be met

### **DESCRIPTION**

The VS-10ETF..S-M3 fast soft recovery rectifier series has been optimized for combined short reverse recovery time and low forward voltage drop.

The glass passivation ensures stable reliable operation in the most severe temperature and power cycling conditions.

MAJOR RATINGS AND CHARACTERISTICS						
SYMBOL	VALUES	UNITS				
I <sub>F(AV)</sub>	Sinusoidal waveform	10	А			
V <sub>RRM</sub>		1000, 1200	V			
I <sub>FSM</sub>		155	А			
V <sub>F</sub>	10 A, T <sub>J</sub> = 25 °C	1.33	V			
t <sub>rr</sub>	1 A, 100 A/μs	80	ns			
T <sub>J</sub>	Range	-40 to +150	°C			

VOLTAGE RATINGS						
PART NUMBER	V <sub>RRM</sub> , MAXIMUM PEAK REVERSE VOLTAGE V	V <sub>RSM</sub> , MAXIMUM NON-REPETITIVE PEAK REVERSE VOLTAGE V	I <sub>RRM</sub> AT 150 °C mA			
VS-10ETF10S-M3	1000	1100	1			
VS-10ETF12S-M3	1200	1300	4			

ABSOLUTE MAXIMUM RATINGS						
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS		
Maximum average forward current	I <sub>F(AV)</sub>	T <sub>C</sub> = 125 °C, 180° conduction half sine wave	10			
Maximum peak one cycle non-repetitive	I <sub>FSM</sub>	10 ms sine pulse, rated V <sub>RRM</sub> applied	130	Α		
surge current		10 ms sine pulse, no voltage reapplied	155			
Maximum 12t for fusing	l <sup>2</sup> t	10 ms sine pulse, rated V <sub>RRM</sub> applied	85	A <sup>2</sup> s		
Maximum I <sup>2</sup> t for fusing	1-1	10 ms sine pulse, no voltage reapplied	120	A-S		
Maximum I <sup>2</sup> √t for fusing	I <sup>2</sup> √t	t = 0.1 ms to 10 ms, no voltage reapplied	1200	A²√s		

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ELECTRICAL SPECIFICATIONS						
PARAMETER	SYMBOL	TEST CO	NDITIONS	VALUES	UNITS	
Maximum forward voltage drop	$V_{FM}$	10 A, T <sub>J</sub> = 25 °C		1.33	V	
Forward slope resistance	r <sub>t</sub>	T <sub>.1</sub> = 150 °C	22.9	mΩ		
Threshold voltage	V <sub>F(TO)</sub>	1J = 150 C		0.96	V	
Maximum various lastrage cumumt		T <sub>J</sub> = 25 °C	\/	0.1	A	
Maximum reverse leakage current	IRM	T <sub>J</sub> = 150 °C	$V_R$ = rated $V_{RRM}$	4	mA	

RECOVERY CHARACTERISTICS						
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS	· •	
Reverse recovery time	t <sub>rr</sub>	L- at 10 A	310	ns	I <sub>FM</sub>	
Reverse recovery current	I <sub>rr</sub>	I <sub>F</sub> at 10 A <sub>pk</sub> 25 Α/μs	4.7	Α		
Reverse recovery charge	Q <sub>rr</sub>	25 °C	1.05	μC	dir/ Q <sub>rr</sub>	
Typical snap factor	S		0.6		I <sub>RM(REC)</sub>	

THERMAL - MECHANICAL SPECIFICATIONS					
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS	
Maximum junction and storage temperature range	T <sub>J</sub> , T <sub>Stg</sub>		-40 to +150	°C	
Maximum thermal resistance, junction to case	R <sub>thJC</sub>	DC operation	1.5	°C/W	
Maximum thermal resistance, junction to ambient (PCB mount)	R <sub>thJA</sub> (1)		62	- C/VV	
Approximate weight			2	g	
Approximate weight			0.07	OZ.	
Marking davisa		Case style D <sup>2</sup> PAK (TO-263AB)	10ETF	=10S	
Marking device		Case Style D-PAR (10-203AB)	10ETF12S		

#### Note

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<sup>(1)</sup> When mounted on 1" square (650 mm²) PCB of FR-4 or G-10 material 4 oz. (140 μm) copper 40 °C/W. For recommended footprint and soldering techniques refer to application note #AN-994





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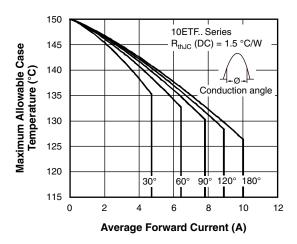


Fig. 1 - Current Rating Characteristics

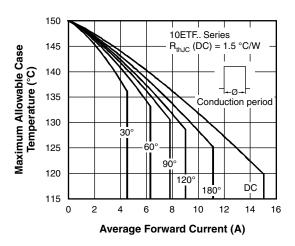


Fig. 2 - Current Rating Characteristics

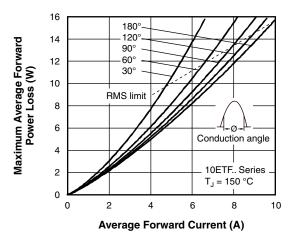


Fig. 3 - Forward Power Loss Characteristics

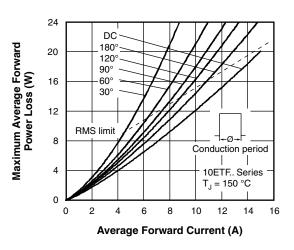


Fig. 4 - Forward Power Loss Characteristics

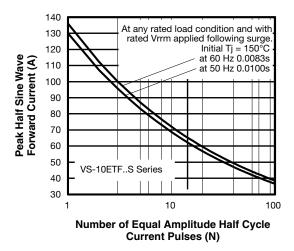


Fig. 5 - Maximum Non-Repetitive Surge Current

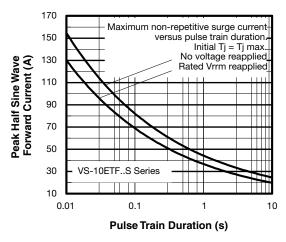


Fig. 6 - Maximum Non-Repetitive Surge Current

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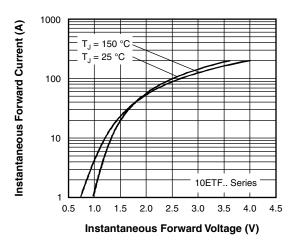


Fig. 7 - Forward Voltage Drop Characteristics

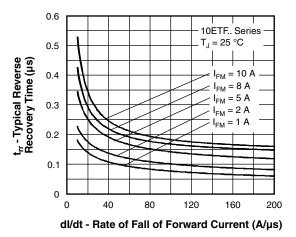


Fig. 8 - Recovery Time Characteristics, T<sub>J</sub> = 25 °C

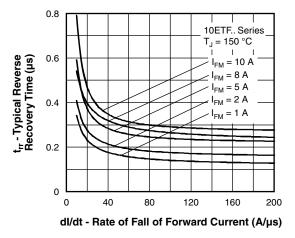


Fig. 9 - Recovery Time Characteristics, T<sub>J</sub> = 150 °C

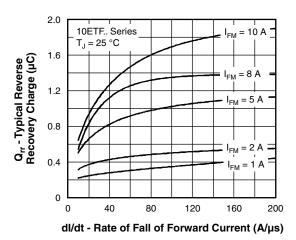


Fig. 10 - Recovery Charge Characteristics,  $T_J = 25$  °C

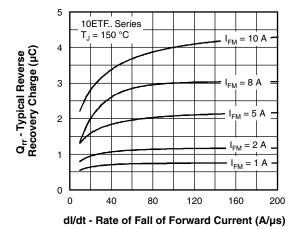


Fig. 11 - Recovery Charge Characteristics, T<sub>J</sub> = 150 °C

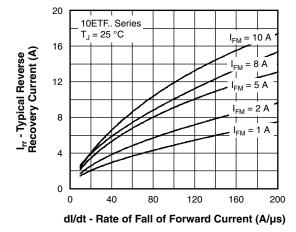


Fig. 12 - Recovery Current Characteristics, T<sub>J</sub> = 25 °C

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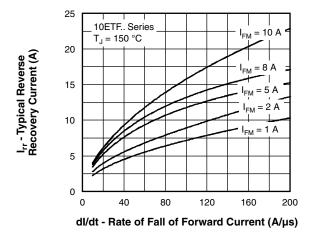


Fig. 13 - Recovery Current Characteristics,  $T_J = 150 \, ^{\circ}\text{C}$ 

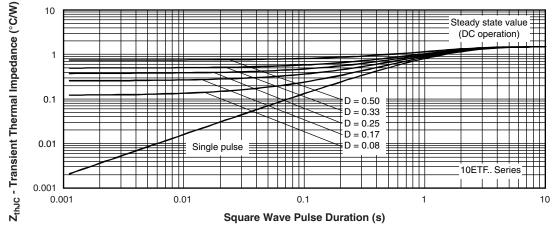


Fig. 14 - Thermal Impedance Z<sub>thJC</sub> Characteristics

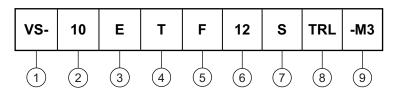


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### **ORDERING INFORMATION TABLE**

**Device code** 



1 - Vishay Semiconductors product

2 - Current rating (10 = 10 A)

Circuit configuration:

E = single

4 - Package:

 $T = D^2PAK (TO-263AB)$ 

5 - Type of silicon:

F = fast soft recovery rectifier

- Voltage code x 100 = V<sub>RRM</sub> - 10 = 1000 V 12 = 1200 V

7 - S = surface mountable

8 - • None = tube

• TRR = tape and reel (right oriented)

• TRL = tape and reel (left oriented)

9 - -M3 = halogen-free, RoHS-compliant, and terminations lead (Pb)-free

ORDERING INFORMATION (Example)					
PREFERRED P/N	BASE QUANTITY	PACKAGING DESCRIPTION			
VS-10ETF10S-M3	50	Antistatic plastic tubes			
VS-10ETF10STRR-M3	800	13" diameter reel			
VS-10ETF10STRL-M3	800	13" diameter reel			
VS-10ETF12S-M3	50	Antistatic plastic tubes			
VS-10ETF12STRR-M3	800	13" diameter reel			
VS-10ETF12STRL-M3	800	13" diameter reel			

LINKS TO RELATED DOCUMENTS					
Dimensions	www.vishay.com/doc?96164				
Part marking information	www.vishay.com/doc?95444				
Packaging information	www.vishay.com/doc?96424				

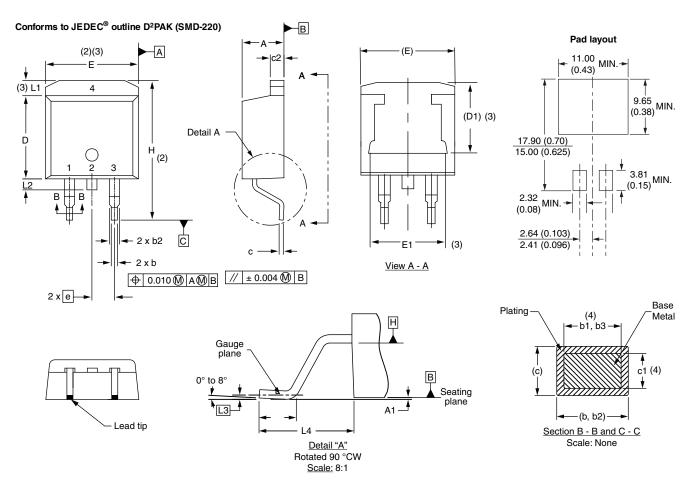
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## D<sup>2</sup>PAK

### **DIMENSIONS** in millimeters and inches



SYMBOL	MILLIMETERS		INCHES		NOTES
STWIBUL	MIN.	MAX.	MIN.	MAX.	NOIES
Α	4.06	4.83	0.160	0.190	
A1	0.00	0.254	0.000	0.010	
b	0.51	0.99	0.020	0.039	
b1	0.51	0.89	0.020	0.035	4
b2	1.14	1.78	0.045	0.070	
b3	1.14	1.73	0.045	0.068	4
С	0.38	0.74	0.015	0.029	
c1	0.38	0.58	0.015	0.023	4
c2	1.14	1.65	0.045	0.065	
D	8.51	9.65	0.335	0.380	2

SYMBOL	MILLIM	IETERS	INC	HES	NOTES
STINIBOL	MIN.	MAX.	MIN.	MAX.	NOTES
D1	6.86	8.00	0.270	0.315	3
Е	9.65	10.67	0.380	0.420	2, 3
E1	7.90	8.80	0.311	0.346	3
е	2.54 BSC		0.100	BSC	
Н	14.61	15.88	0.575	0.625	
L	1.78	2.79	0.070	0.110	
L1	-	1.65	-	0.066	3
L2	1.27	1.78	0.050	0.070	
L3	0.25 BSC		0.010	BSC	
L4	4.78	5.28	0.188	0.208	

### Notes

- (1) Dimensioning and tolerancing per ASME Y14.5 M-1994
- (2) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outmost extremes of the plastic body
- (3) Thermal pad contour optional within dimension E, L1, D1 and E1
- (4) Dimension b1 and c1 apply to base metal only
- (5) Datum A and B to be determined at datum plane H
- (6) Controlling dimension: inches
- (7) Outline conforms to JEDEC® outline TO-263AB

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